



STS10N3LH5

N-channel 30 V, 0.019 Ω , 10 A, SO-8
STripFET™ V Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
STS10N3LH5	30 V	0.021 Ω	10 A

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- Very low switching gate charge
- High avalanche ruggedness
- Low gate drive power losses

Application

- Switching applications

Description

This STripFET™V Power MOSFET technology is among the latest improvements, which have been especially tailored to achieve very low on-state resistance providing also one of the best-in-class FOM.

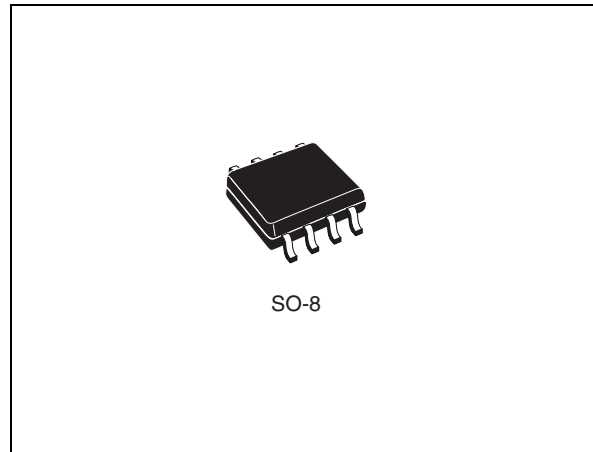


Figure 1. Internal schematic diagram

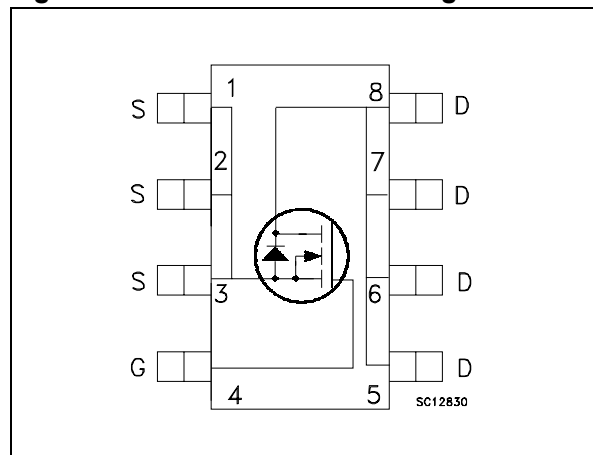


Table 1. Device summary

Order codes	Marking	Package	Packaging
STS10N3LH5	10D3L	SO-8	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{GS}	Gate-Source voltage	± 22	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	10	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	7	A
$I_{DM}^{(2)}$	Drain current (pulsed)	40	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	2.5	W
	Derating factor	0.02	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	50	mJ
T_J T_{stg}	Operating junction temperature Storage temperature	- 55 to 150	$^\circ\text{C}$

1. Limited by wire bonding
2. Pulse width limited by safe operating area
3. Starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = 21\text{ A}$, $L = 0.2\text{ mH}$

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case max	50	$^\circ\text{C}/\text{W}$
R_{thJA}	Thermal resistance junction-case max	100	$^\circ\text{C}/\text{W}$
T_J	Maximum lead temperature for soldering purpose	275	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 30\text{ V}$ $V_{DS} = 30\text{ V}$, $T_c = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 22\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 5\text{ A}$		0.019	0.021	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 5\text{ A}$		0.023	0.028	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	475	-	pF
C_{oss}	Output capacitance			97		pF
C_{rss}	Reverse transfer capacitance			19		pF
Q_g	Total gate charge	$V_{DD} = 15\text{ V}$, $I_D = 10\text{ A}$	-	4.6	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 5\text{ V}$		1.7		nC
Q_{gd}	Gate-drain charge	(<i>Figure 14</i>)		1.9		nC
Q_{gs1}	Pre V_{th} gate-to-source charge	$V_{DD} = 15\text{ V}$, $I_D = 10\text{ A}$	-	0.67	-	nC
Q_{gs2}	Post V_{th} gate-to-source charge	$V_{GS} = 5\text{ V}$ (<i>Figure 19</i>)		0.84		nC
R_G	Gate input resistance	$f = 1\text{ MHz}$ gate bias Bias = 0 test signal level = 20 mV open drain	-	2.5	-	Ω

Table 6. Switching on/off (resistive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 15\text{ V}$, $I_D = 5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ <i>(Figure 13 and Figure 18)</i>	-	4 22	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD} = 15\text{ V}$, $I_D = 5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ <i>(Figure 13 and Figure 18)</i>	-	13 2.8	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		10 40	A A
V_{SD}	Forward on voltage	$I_{SD} = 5\text{ A}$, $V_{GS} = 0$	-		1.1	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 10\text{ A}$, $V_{DD} = 25\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, <i>(Figure 15)</i>	-	16.2 7.8 1		ns nC A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

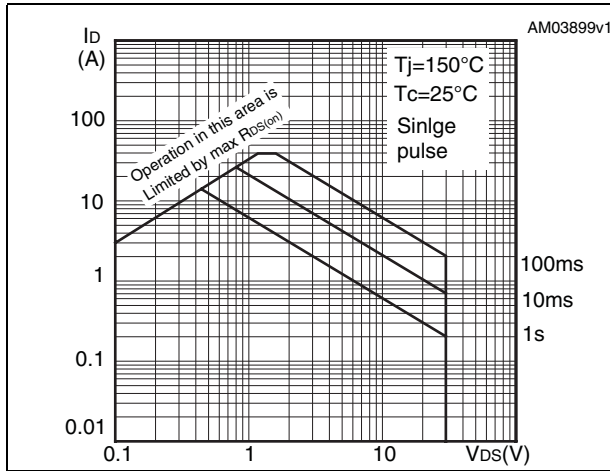


Figure 3. Thermal impedance

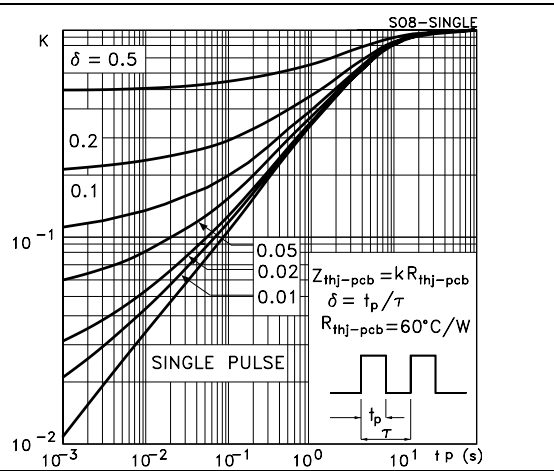


Figure 4. Output characteristics

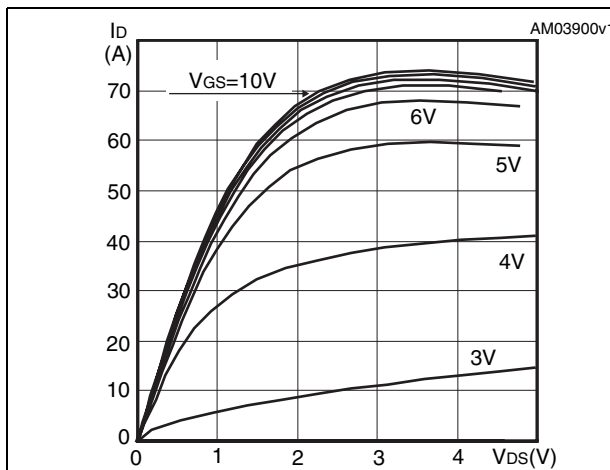


Figure 5. Transfer characteristics

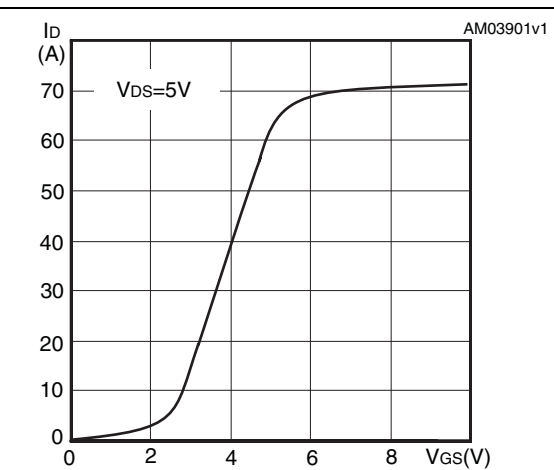


Figure 6. Normalized BV_{DSS} vs temperature

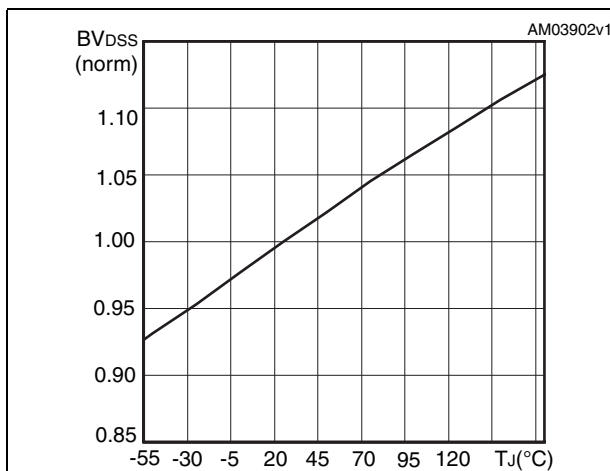


Figure 7. Static drain-source on resistance

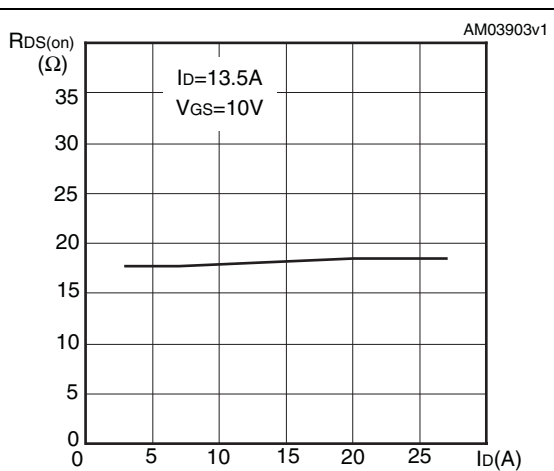


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

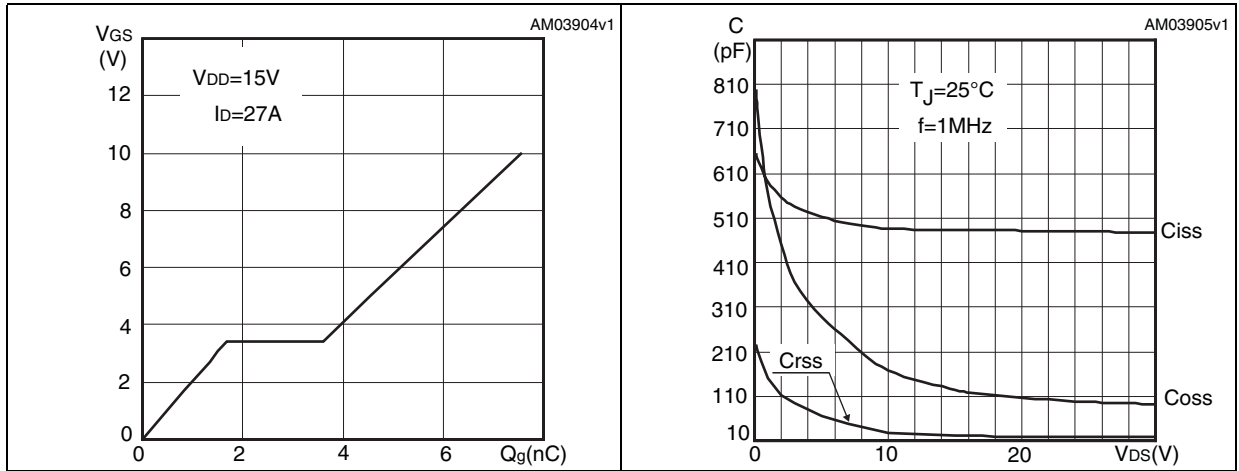


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

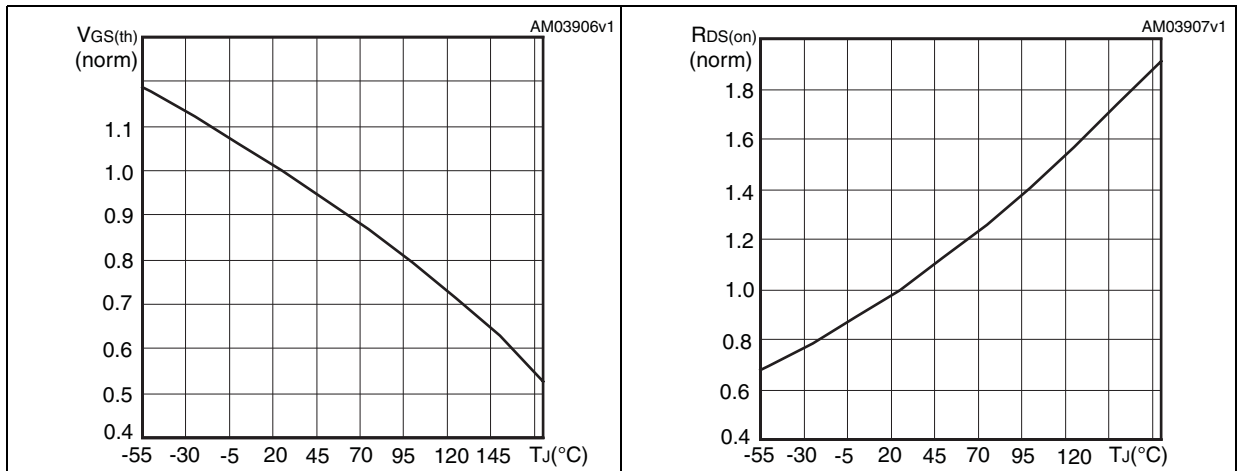
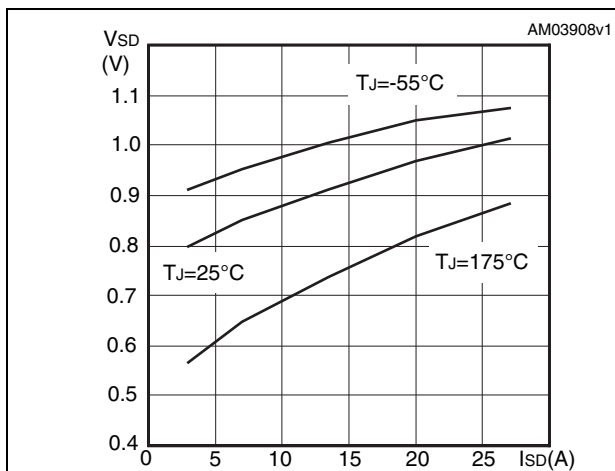
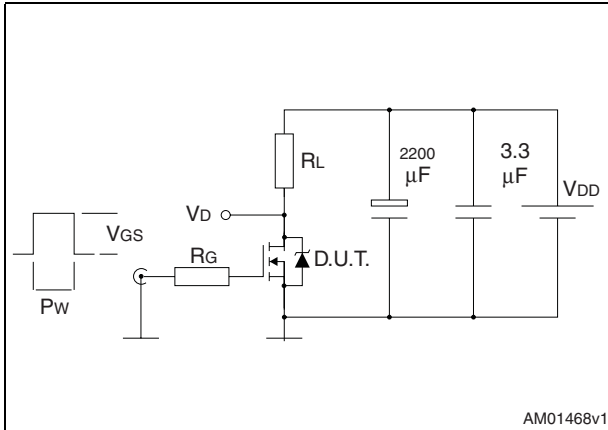


Figure 12. Source-drain diode forward characteristics



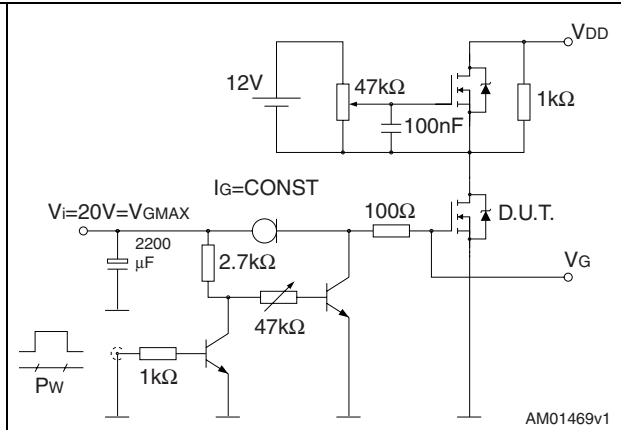
3 Test circuits

Figure 13. Switching times test circuit for resistive load



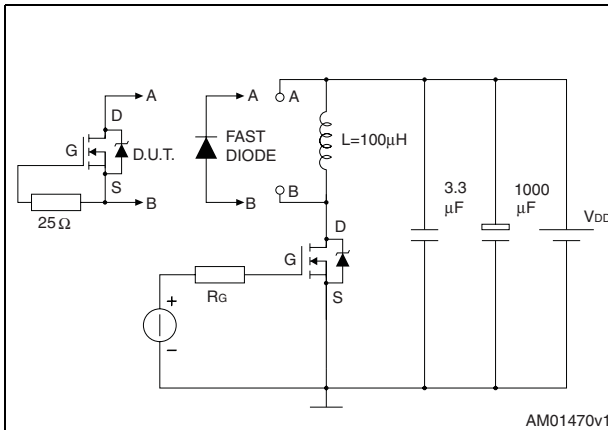
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Figure 14. Gate charge test circuit



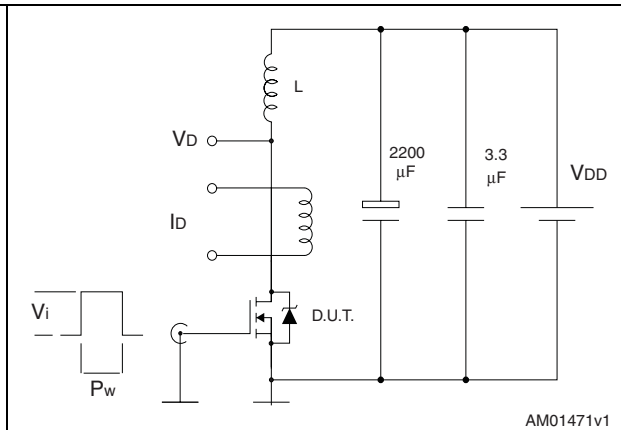
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Figure 15. Test circuit for inductive load switching and diode recovery times



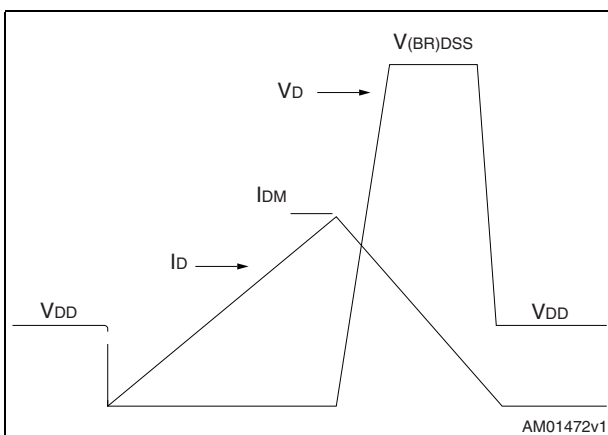
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Figure 16. Unclamped inductive load test circuit



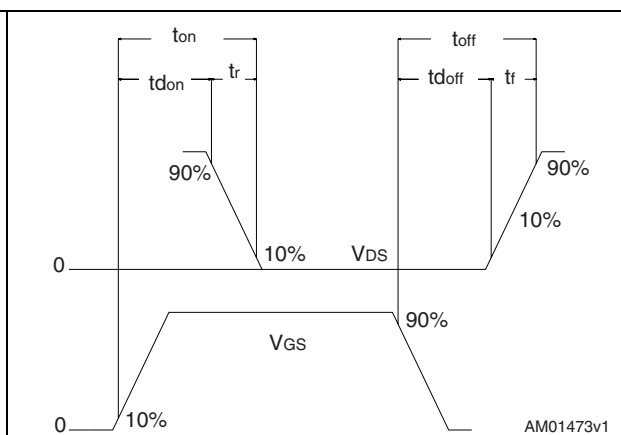
AM01471v1

Figure 17. Unclamped inductive waveform



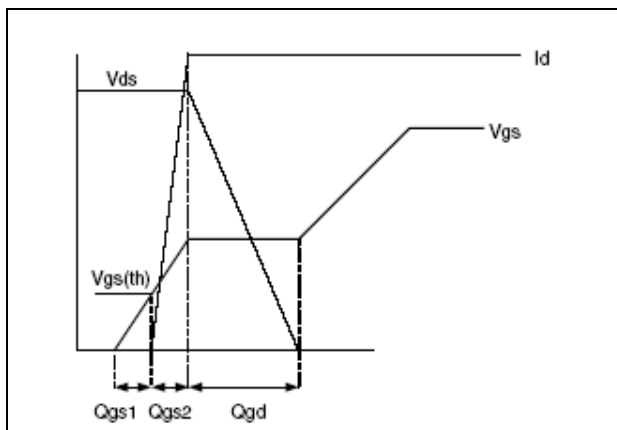
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Figure 18. Switching time waveform



AM01473v1

Figure 19. Gate charge waveform

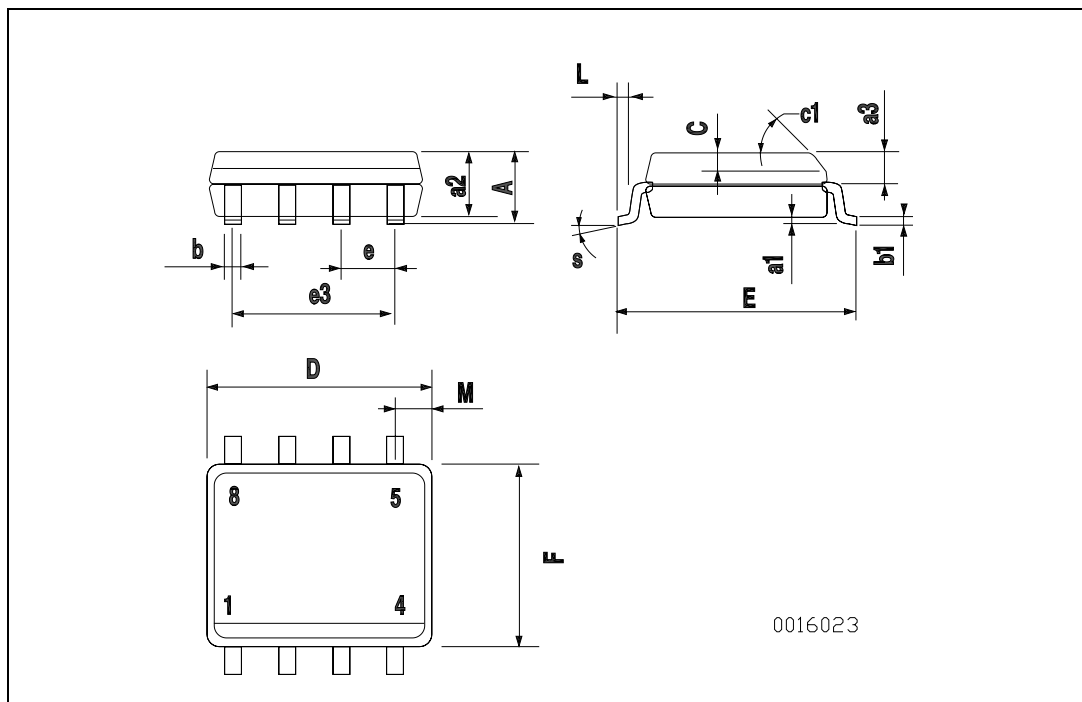


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



5 Revision history

Table 8. Document revision history

Date	Revision	Changes
06-May-2009	1	First release

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